## NPN Silicon Epitaxial Planar Transistor

for use in driver stage of high voltage audio equipments.

The transistor is subdivided into three groups, M, L and K , according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.


1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19 g

Absolute Maximum Ratings ( $\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}$ )

|  | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: |
| Collector Base Voltage | $\mathrm{V}_{\text {CBO }}$ | 60 | V |
| Collector Emitter Voltage | $\mathrm{V}_{\text {CEO }}$ | 60 | V |
| Emitter Base Voltage | $\mathrm{V}_{\text {EBO }}$ | 5 | V |
| Collector Current | $\mathrm{I}_{\mathrm{C}}$ | 300 | mA |
| Base Current | $\mathrm{I}_{\mathrm{B}}$ | 60 | mA |
| Power Dissipation | $\mathrm{P}_{\text {tot }}$ | 600 | mW |
| Junction Temperature | $\mathrm{T}_{\mathrm{j}}$ | 150 | ${ }^{\circ} \mathrm{C}$ |
| Storage Temperature Range | $\mathrm{T}_{\mathrm{S}}$ | $-55 \mathrm{to}+150$ | ${ }^{\circ} \mathrm{C}$ |

Characteristics at $\mathrm{Tamb}=25^{\circ} \mathrm{C}$

|  | Symbol | Min. | Typ. | Max. | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| DC Current Gain <br> at $\mathrm{V}_{\mathrm{CE}}=1 \mathrm{~V}, \mathrm{I}_{\mathrm{C}}=50 \mathrm{~mA}$ <br> Current Gain Group M <br> at $\mathrm{V}_{\mathrm{CE}}=2 \mathrm{~V}, \mathrm{I}_{\mathrm{C}}=300 \mathrm{~mA}$ | $\begin{aligned} & \mathrm{h}_{\mathrm{FE}} \\ & \mathrm{~h}_{\mathrm{FE}} \\ & \mathrm{~h}_{\mathrm{FE}} \\ & \mathrm{~h}_{\mathrm{F}} \end{aligned}$ | $\begin{gathered} 90 \\ 135 \\ 200 \\ 30 \end{gathered}$ | 80 | $\begin{aligned} & 180 \\ & 270 \\ & 400 \end{aligned}$ |  |
| Base Emitter Voltage at $\mathrm{I}_{\mathrm{C}}=10 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=6 \mathrm{~V}$ | $V_{\text {be }}$ | 600 | 645 | 700 | mV |
| Emitter Cutoff Current <br> at $\mathrm{V}_{\mathrm{EB}}=5 \mathrm{~V}$ | $\mathrm{I}_{\text {Ebo }}$ | - | - | 100 | nA |
| Collector Cutoff Current at $\mathrm{V}_{\mathrm{CB}}=60 \mathrm{~V}$ | $\mathrm{I}_{\text {cво }}$ | - | - | 100 | nA |
| Collector Saturation Voltage at $\mathrm{I}_{\mathrm{C}}=300 \mathrm{~mA}, \mathrm{I}_{\mathrm{B}}=30 \mathrm{~mA}$ | $\mathrm{V}_{\text {CE(sat) }}$ | - | 0.15 | 0.6 | V |
| Base Saturation Voltage at $\mathrm{I}_{\mathrm{C}}=300 \mathrm{~mA}, \mathrm{I}_{\mathrm{B}}=30 \mathrm{~mA}$ | $\mathrm{V}_{\mathrm{BE} \text { (sat) }}$ | - | 0.86 | 1.2 | V |
| Gain Bandwidth Product at $V_{C E}=6 \mathrm{~V}, \mathrm{I}_{\mathrm{E}}=-10 \mathrm{~mA}$ | $\mathrm{f}_{\text {T }}$ | 50 | 140 | - | MHz |
| Collector to Base Capacitance at $\mathrm{V}_{\mathrm{CB}}=6 \mathrm{~V}, \mathrm{f}=1 \mathrm{MHz}$ | $\mathrm{C}_{\text {ов }}$ | - | 7.0 | 15 | pF |

